

Claims

1. A heat dissipating IC device comprising:
5 at least one IC die comprising a semiconductor substrate including at least one circuitry layer with a hot region on at least one substrate face, a backside and a perimeter;
a doped region diffused within the semiconductor
10 substrate backside thereby creating a depletion layer between the substrate and doped region; and
a voltage connected to the doped region, whereby the charge carrier flow, through the doped region of the substrate, travels in a direction from the hot region on the
15 semiconductor substrate face outward toward the perimeter of the substrate face.
2. The device in claim 1 wherein an electric via connects a portion of the circuitry layer with the doped
20 region within the semiconductor substrate in order to provide electrical power.
3. The device in claim 1 wherein the doped region within the semiconductor substrate is electrically in series
25 with an electrical load other than itself.
4. The device in claim 1 wherein the doped region within the semiconductor substrate is utilized as a resistive load for an electronic component or power supply circuit.
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5. A heat dissipating IC device comprising:
at least one IC die comprising a semiconductor substrate including at least one circuitry layer with a hot region on at least one substrate face;
35 at least one electrically conductive or semiconductive member attachable to the semiconductor substrate; and

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an electrical source connected to the electrically conductive or semiconductive member, whereby the charge carrier flow travels in a direction from the hotter region on the semiconductor substrate face outward toward the perimeter of the substrate face.

6. The device in claim 5 wherein an electric via connects a portion of the circuitry layer with the semiconductor substrate in order to provide electrical power to the electrically conductive member.

7. The device in claim 5 wherein the electrically conductive member is electrically in series with an electrical load other than itself.

8. The device in claim 5 wherein the electrically conductive member is utilized as a resistive load for an electronic component.

9. The device in claim 5, further comprising a package for housing an IC die.

10. The device in claim 5 wherein the semiconductor substrate is attached to the electrically conductive or semiconductive member by wafer bonding.

11. The device in claim 5 wherein the electrically conductive or semiconductive member is attached to more than one semiconductor substrate.

12. The device in claim 5 wherein the semiconductor substrate attachment to the conductive or semiconductive member is electrically conductive.

13. A heat dissipating IC device comprising:
at least one IC die comprising a semiconductor substrate including at least one circuitry layer on at least one substrate face;

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at least one thermoelement couple, said couple comprised of the semiconductor substrate and at least one dissimilar conductor electrically bonded to the semiconductor substrate thereby creating junctions; and

5 said thermoelement couple comprises at least one heat absorbing junction and at least one heat rejecting junction wherein the heat absorbing junction is positioned near the center of the substrate face and the heat rejecting junction is positioned near the perimeter of the substrate
10 face.

14. The device in claim 13 wherein the semiconductor substrate, adjacent the junctions, includes a doped region thereby creating a depletion layer between the
15 substrate and doped region.

15. The device in claim 13 wherein the dissimilar conductor comprises more than one layer.

20 16. The device in claim 13 wherein an electric via connects a portion of the circuitry layer with the semiconductor substrate in order to provide electrical power to the thermoelement couple junctions.

25 17. The device in claim 13 wherein a voltage is applied to the thermoelement couple.

30 18. The device in claim 13 wherein the thermoelement couple is electrically in series with an electrical load other than itself.

35 19. The device in claim 13 wherein the thermoelement couple is utilized as a resistor for an electronic component.

20. The device in claim 13 wherein a voltage and current is generated by the thermoelement couple and is consumed by an external electric load.

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21. The device in claim 13 wherein the silicon substrate and dissimilar thermoelement, comprising each thermoelement couple, is electrically bonded to each other at both the heat absorbing and heat rejecting junctions thereby creating closed electrical circuit thermoelement couples.

22. A heat dissipating IC device including at least one IC die comprising a semiconductor substrate including at least one circuitry layer, the substrate attachable to a heat sink/spreader structure comprising:

a heat sink/spreader structure wherein at least one thermoelement couple is created through the bonding between at least one semiconductor to at least one dissimilar conductor; and

the dissimilar conductor comprises at least one heat absorbing junction and one heat rejecting junction.

23. The device in claim 22 wherein the heat absorbing junction is positioned near the center of the device and the heat rejecting junction is positioned near the perimeter of the device.

24. The device in claim 22 wherein the dissimilar conductor and semiconductor each comprise more than one layer.

25. The device in claim 22, further comprising a package for housing an IC die.

26. The device in claim 22 wherein the semiconductor substrate is attached to the heat sink/spreader structure by wafer bonding.

27. The device in claim 22 wherein the heat sink/spreader structure face to be wafer bonded is larger in overall area than the semiconductor substrate.

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28. The device in claim 22 wherein the heat rejecting junctions are located outside the bond line between the semiconductor substrate and heat sink/spreader structure.

29. The device in claim 22 wherein the heat sink/spreader structure is attached to more than one semiconductor substrate.

30. The device in claim 22 wherein a voltage is applied to the thermoelement couple.

31. The device in claim 22 wherein the thermoelement couple is electrically in series with an electrical load other than itself.

32. The device in claim 22 wherein the thermoelement couple is utilized as a resistive load for an electronic component.

33. The device in claim 22 wherein a voltage and current is generated by the thermoelement couple and is consumed by an external electric load.

34. The device in claim 22 wherein the semiconductor substrate attachment to the heat sink/spreader structure is electrically conductive.

35. A method of manufacturing a heat dissipating IC device including at least one IC die comprising a semiconductor substrate including at least one circuitry layer on at least one substrate face, more than one thermoelement couple, each with at least one heat absorbing and one heat rejecting junction and P-type and N-type conductive dopants comprising:

(a) Selectively depositing the P and N-type dopants into at least one face of the substrate to form a pattern of P and N-type conductive thermoelements within the semiconductor substrate;

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(b) Electrically bonding the P and N-type conductivity thermoelements at heat absorbing and heat rejecting junctions to form thermoelement couples.

5 36. The method of claim 35 wherein the heat absorbing junctions are positioned near the center of the semiconductor substrate face and the heat rejecting junctions are positioned near the perimeter of the substrate face.

10 37. The method of claim 35 wherein a dielectric, such as oxide or nitride, is added to the physical regions between each P and N-type thermoelement in order to provide electrical insulation between each thermoelement.

15 38. The method of claim 35 wherein the physical regions between each P and N-type thermoelement are removed in order to provide electrical insulation between each thermoelement.

20 39. The method of claim 35 wherein a voltage is applied to at least one thermoelement couple.

25 40. The method of claim 35 wherein at least one thermoelement couple is electrically in series with an electrical load other than itself.

30 41. The method of claim 35 wherein at least one thermoelement couple is utilized as a resistive load for an electronic component.

35 42. The method of claim 35 wherein a voltage and current is generated by at least one thermoelement couple and is consumed by an external electric load.

40 43. A heat dissipating IC device including at least one IC die comprising at least one semiconductor substrate including at least one circuitry layer on at least one substrate face, more than one thermoelement couple stage,

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51. The device in claim 43 wherein a voltage and current is generated by at least one thermoelement couple and is consumed by an external electric load.

52. The device in claim 43 wherein each dissimilar thermoelement, comprising each thermoelement couple, is electrically bonded to each other at both the heat absorbing and heat rejecting junctions thereby creating closed electrical circuit thermoelement couples.

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